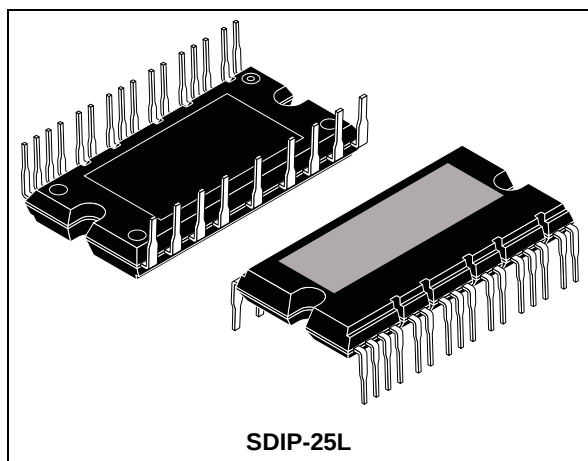


SLLIMM™ small low-loss intelligent molded module IPM, 3-phase inverter, 10 A, 600 V short-circuit rugged IGBT

Datasheet - production data



Features

- IPM 10 A, 600 V 3-phase IGBT inverter bridge including control ICs for gate driving and free-wheeling diodes
- Short-circuit rugged IGBTs
- $V_{CE(sat)}$ negative temperature coefficient
- 3.3 V, 5 V, 15 V CMOS/TTL inputs comparators with hysteresis and pull-down / pull-up resistors
- Undervoltage lockout
- Internal bootstrap diode
- Interlocking function
- Shutdown function
- DBC substrate leading to low thermal resistance
- Isolation rating of 2500 V_{rms}/min
- 4.7 kΩ NTC for temperature control
- UL recognized: UL1557 file E81734

Applications

- 3-phase inverters for motor drives
- Home appliances, such as washing machines, refrigerators, air conditioners and sewing machines

Description

This intelligent power module provides a compact, high performance AC motor drive in a simple, rugged design. Combining ST proprietary control ICs with the most advanced short-circuit-rugged IGBT system technology, this device is ideal for 3-phase inverters in applications such as home appliances and air conditioners. SLLIMM™ is a trademark of STMicroelectronics.

Table 1. Device summary

Order code	Marking	Package	Packing
STGIPS10K60T-H	GIPS10K60T-H	SDIP-25L	Tube

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1 Internal block diagram and pin configuration

Figure 1. Internal block diagram

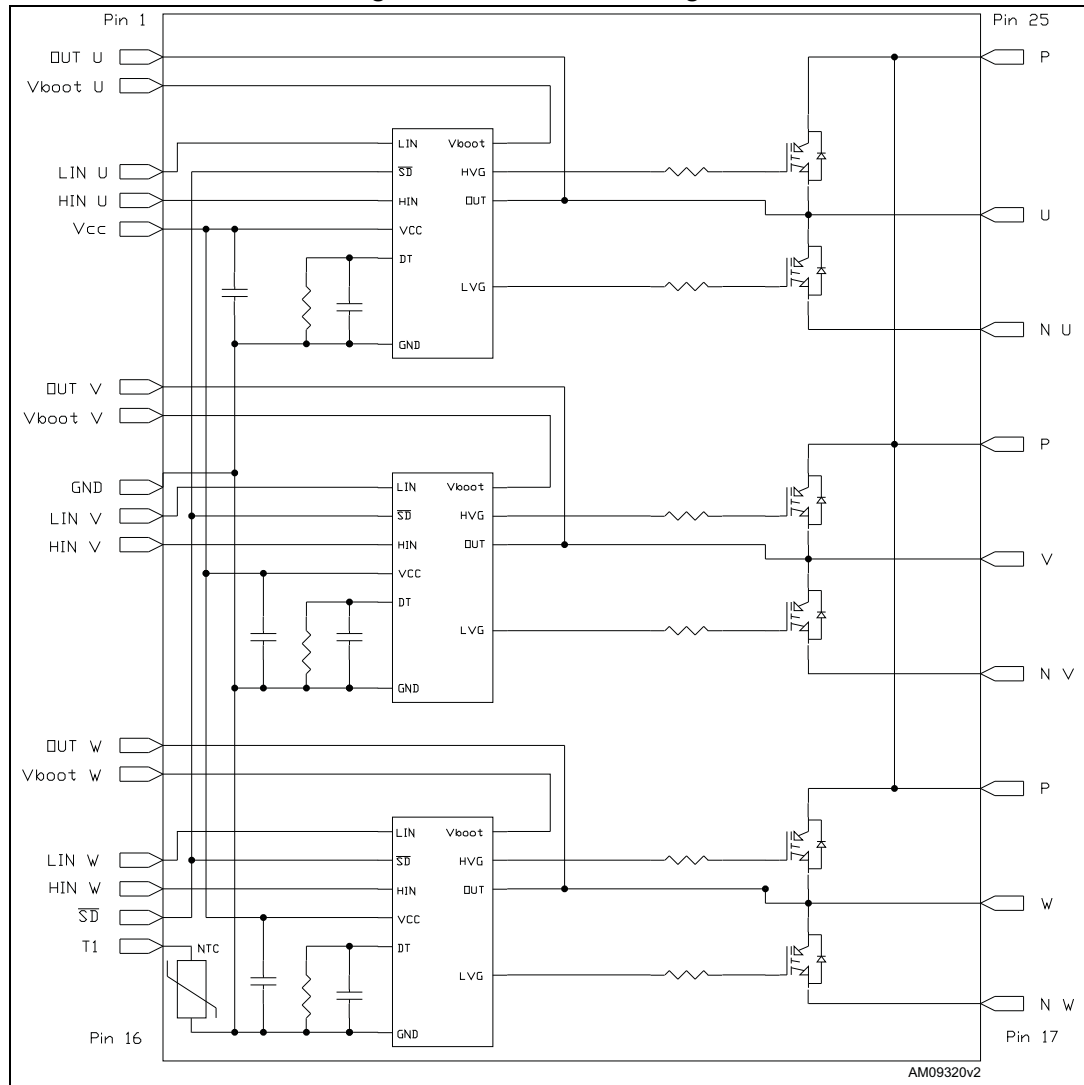
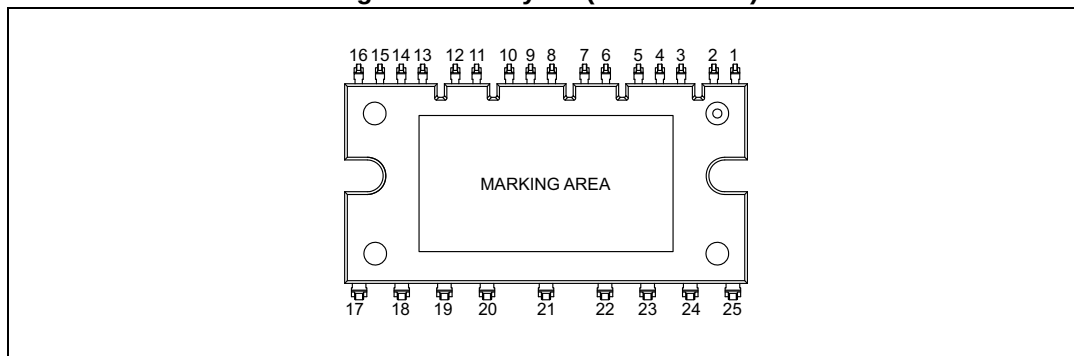


Table 2. Pin description

Pin n°	Symbol	Description
1	OUT _U	High side reference output for U phase
2	V _{boot U}	Bootstrap voltage for U phase
3	LIN _U	Low side logic input for U phase
4	HIN _U	High side logic input for U phase
5	V _{CC}	Low voltage power supply
6	OUT _V	High side reference output for V phase
7	V _{boot V}	Bootstrap voltage for V phase
8	GND	Ground
9	LIN _V	Low side logic input for V phase
10	HIN _V	High side logic input for V phase
11	OUT _W	High side reference output for W phase
12	V _{boot W}	Bootstrap voltage for W phase
13	LIN _W	Low side logic input for W phase
14	HIN _W	High side logic input for W phase
15	SD	Shut down logic input (active low)
16	T1	NTC thermistor terminal
17	N _W	Negative DC input for W phase
18	W	W phase output
19	P	Positive DC input
20	N _V	Negative DC input for V phase
21	V	V phase output
22	P	Positive DC input
23	N _U	Negative DC input for U phase
24	U	U phase output
25	P	Positive DC input

Figure 2. Pin layout (bottom view)



2 Electrical ratings

2.1 Absolute maximum ratings

Table 3. Inverter part

Symbol	Parameter	Value	Unit
V_{PN}	Supply voltage applied between P - N_U , N_V , N_W	450	V
$V_{PN(surge)}$	Supply voltage (surge) applied between P - N_U , N_V , N_W	500	V
V_{CES}	Each IGBT collector emitter voltage ($V_{IN}^{(1)} = 0$)	600	V
$\pm I_C^{(2)}$	Each IGBT continuous collector current at $T_C = 25^\circ\text{C}$	10	A
$\pm I_{CP}^{(3)}$	Each IGBT pulsed collector current	20	A
P_{TOT}	Each IGBT total dissipation at $T_C = 25^\circ\text{C}$	33	W
t_{scw}	Short-circuit withstand time, $V_{CE} = 0.5 V_{(BR)CES}$ $T_j = 125^\circ\text{C}$, $V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN(1)} = 5\text{ V}$	5	μs

1. Applied between HIN_i , LIN_i and G_{ND} for $i = U, V, W$.
2. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

3. Pulse width limited by max junction temperature.

Table 4. Control part

Symbol	Parameter	Min.	Max.	Unit
V_{OUT}	Output voltage applied between OUT_U , OUT_V , OUT_W - GND	$V_{boot} - 21$	$V_{boot} + 0.3$	V
V_{CC}	Low voltage power supply	- 0.3	21	V
V_{boot}	Bootstrap voltage	- 0.3	620	V
V_{IN}	Logic input voltage applied between HIN , LIN and GND	- 0.3	15	V
V_{SD}	Open drain voltage	- 0.3	15	V
dV_{OUT}/dt	Allowed output slew rate		50	V/ns

Table 5. Total system

Symbol	Parameter	Value	Unit
V_{ISO}	Isolation withstand voltage applied between each pin and heatsink plate (AC voltage, $t = 60\text{ sec.}$)	2500	V
T_C	Module case operation temperature	-40 to 125	$^\circ\text{C}$
T_J	Power chips operating junction temperature	-40 to 150	$^\circ\text{C}$

2.2 Thermal data

Table 6. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case single IGBT max.	3.8	°C/W
	Thermal resistance junction-case single diode max.	5.5	°C/W

3 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 7. Inverter part

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN(1)} = 5\text{ V}$, $I_C = 5\text{ A}$	-	2.1	2.5	V
		$V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN(1)} = 5\text{ V}$, $I_C = 5\text{ A}$, $T_J = 125\text{ °C}$	-	1.8		
I_{CES}	Collector-cut off current ($V_{IN(1)} = 0$ "logic state")	$V_{CE} = 550\text{ V}$ $V_{CC} = V_{boot} = 15\text{ V}$	-		150	μA
V_F	Diode forward voltage	($V_{IN(1)} = 0$ "logic state"), $I_C = 5\text{ A}$	-		1.9	V
Inductive load switching time and energy						
t_{on}	Turn-on time	$V_{DD} = 300\text{ V}$, $V_{CC} = V_{boot} = 15\text{ V}$, $V_{IN(1)} = 0 \div 5\text{ V}$, $I_C = 5\text{ A}$ (see Figure 4)	-	320	-	ns
$t_{c(on)}$	Crossover time (on)		-	70	-	
t_{off}	Turn-off time		-	430	-	
$t_{c(off)}$	Crossover time (off)		-	135	-	
t_{rr}	Reverse recovery time		-	130	-	
E_{on}	Turn-on switching losses		-	65	-	μJ
E_{off}	Turn-off switching losses		-	75	-	

1. Applied between HIN_i , LIN_i and GND for $i = U, V, W$.

Note: t_{ON} and t_{OFF} include the propagation delay time of the internal drive. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the internally given gate driving condition.

The figure contains two timing diagrams, (a) and (b), illustrating the switching characteristics of a MOSFET.

(a) turn-on: This diagram shows the transition from a low input state to a high input state. The input voltage V_{IN} rises from a low level to a high level $V_{IN(ON)}$. The gate-to-source voltage V_{GS} (labeled V_{CE} in the diagram) follows this rise, showing a delay t_{ON} before it begins to increase. Once it starts rising, it passes through a linear region where the drain current I_C increases linearly from 10% to 90% of its saturation value $I_{C(ON)}$. The time taken for this linear increase is $t_{C(ON)}$. After reaching 90% $I_{C(ON)}$, the current levels off at 100% $I_{C(ON)}$. The output voltage V_{OUT} (labeled V_{CE}) remains at a high level until the current begins to rise, then drops sharply during the linear region and levels off at a low value (10% V_{CE}) after the current has reached 90% $I_{C(ON)}$.

(b) turn-off: This diagram shows the transition from a high input state to a low input state. The input voltage V_{IN} falls from a high level to a low level $V_{IN(OFF)}$. The gate-to-source voltage V_{GS} (labeled V_{CE}) follows this fall, showing a delay t_{OFF} before it begins to decrease. Once it starts decreasing, it passes through a linear region where the drain current I_C decreases linearly from 90% to 10% of its saturation value $I_{C(ON)}$. The time taken for this linear decrease is $t_{C(OFF)}$. After reaching 10% $I_{C(ON)}$, the current levels off at 0% $I_{C(ON)}$. The output voltage V_{OUT} (labeled V_{CE}) remains at a low level until the current begins to decrease, then rises sharply during the linear region and levels off at a high value (10% V_{CE}) after the current has reached 10% $I_{C(ON)}$.



3.1 Control part

Table 8. Low voltage power supply ($V_{CC} = 15\text{ V}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{CC_hys}	V_{CC} UV hysteresis		1.2	1.5	1.8	V
V_{CC_thON}	V_{CC} UV turn ON threshold		11.5	12	12.5	V
V_{CC_thOFF}	V_{CC} UV turn OFF threshold		10	10.5	11	V
I_{qccu}	Undervoltage quiescent supply current	$V_{CC} = 10\text{ V}$ $\overline{SD} = 5\text{ V}$; LIN = 0 V; $H_{IN} = 0$			450	μA
I_{qcc}	Quiescent current	$V_{CC} = 15\text{ V}$ $\overline{SD} = 5\text{ V}$; LIN = 0 V; $H_{IN} = 0$			3.5	mA

Table 9. Bootstrapped voltage ($V_{CC} = 15\text{ V}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{BS_hys}	V_{BS} UV hysteresis		1.2	1.5	1.8	V
V_{BS_thON}	V_{BS} UV turn ON threshold		11.1	11.5	12.1	V
V_{BS_thOFF}	V_{BS} UV turn OFF threshold		9.8	10	10.6	V
I_{QBSU}	Undervoltage V_{BS} quiescent current	$V_{BS} = 9\text{ V}$ $\overline{SD} = 5\text{ V}$; LIN = 0 $H_{IN} = 5\text{ V}$		70	110	μA
I_{QBS}	V_{BS} quiescent current	$V_{BS} = 15\text{ V}$ $\overline{SD} = 5\text{ V}$; LIN = 0 $H_{IN} = 5\text{ V}$		200	300	μA
$R_{DS(on)}$	Bootstrap driver on resistance	LVG ON		120		W

Table 10. Logic inputs ($V_{CC} = 15\text{ V}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{il}	Low logic level voltage		0.8		1.1	V
V_{ih}	High logic level voltage		1.9		2.25	V
I_{HINh}	HIN logic "1" input bias current	HIN = 15 V	20	40	100	μA
I_{HINI}	HIN logic "0" input bias current	HIN = 0 V			1	μA
I_{LINh}	LIN logic "1" input bias current	LIN = 15 V	20	40	100	μA
I_{LINI}	LIN logic "0" input bias current	LIN = 0 V			1	μA
I_{SDh}	$\overline{SD}$ logic "0" input bias current	$\overline{SD} = 15\text{ V}$	30	120	300	μA
I_{SDI}	$\overline{SD}$ logic "1" input bias current	$\overline{SD} = 0\text{ V}$			3	μA
Dt	Dead time	see Figure 9		600		ns

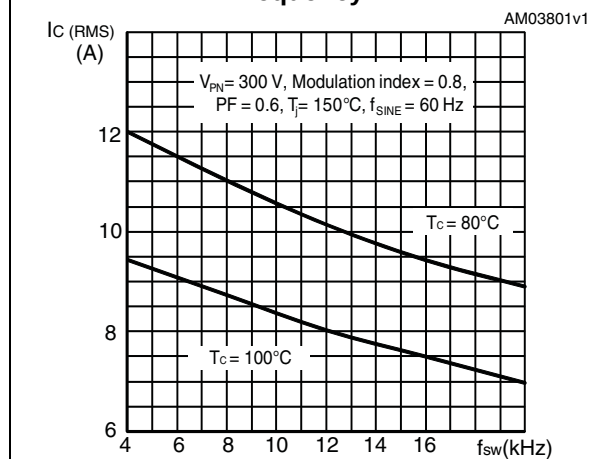
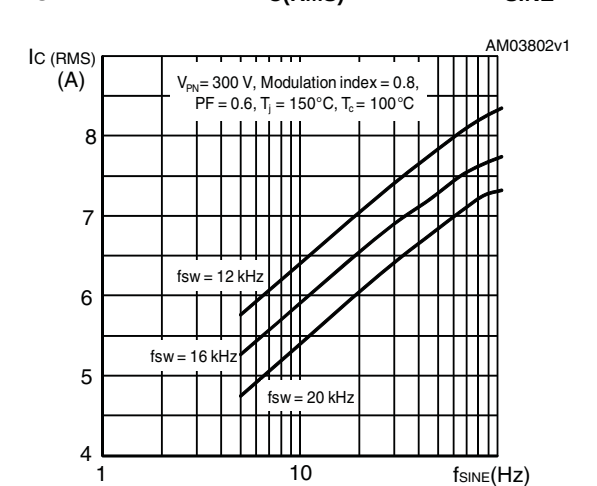
Table 11. Shut down characteristics ($V_{CC} = 15\text{ V}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{sd}	Shut down to high / low side driver propagation delay	$V_{OUT} = 0$, $V_{boot} = V_{CC}$, $V_{IN} = 0$ to 3.3 V	50	125	200	ns

Table 12. Truth table

Condition	Logic input (V_I)			Output	
	SD	LIN	HIN	LVG	HVG
Shutdown enable half-bridge tri-state	L	X	X	L	L
Interlocking half-bridge tri-state	H	H	H	L	L
0 "logic state" half-bridge tri-state	H	L	L	L	L
1 "logic state" low side direct driving	H	H	L	H	L
1 "logic state" high side direct driving	H	L	H	L	H

Note: X: don't care

Figure 5. Maximum $I_{C(RMS)}$ current vs. switching frequency ⁽¹⁾Figure 6. Maximum $I_{C(RMS)}$ current vs. f_{SINE} ⁽¹⁾

1. Simulated curves refer to typical IGBT parameters and maximum R_{thJC} .

3.1.1 NTC thermistor

Table 13. NTC thermistor

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit.
R ₂₅	Resistance	T = 25°C		4.7		kΩ
R ₁₂₅	Resistance	T = 125°C		160		Ω
B	B-constant	T = 25°C to 85°C		3950		K
T	Operating temperature		-40		150	°C

Equation 1: resistance variation vs. temperature

$$R(T) = R_{25} \cdot e^{B\left(\frac{1}{T} - \frac{1}{298}\right)}$$

Where T are temperatures in Kelvins

Figure 7. NTC resistance vs. temperature

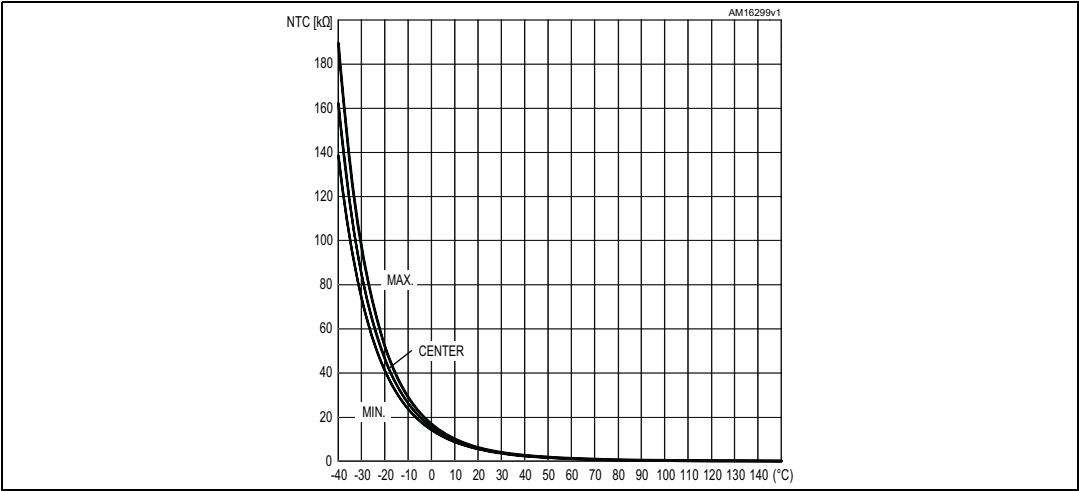
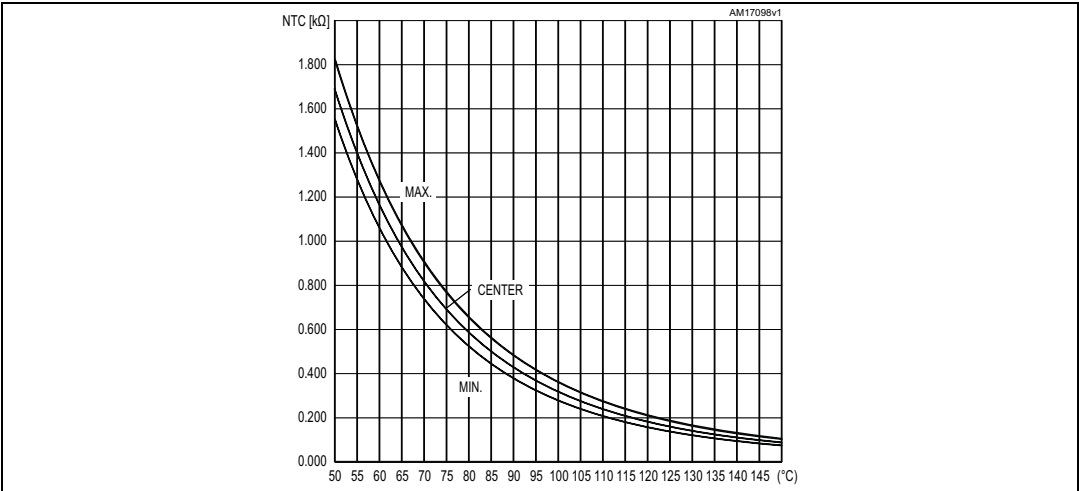
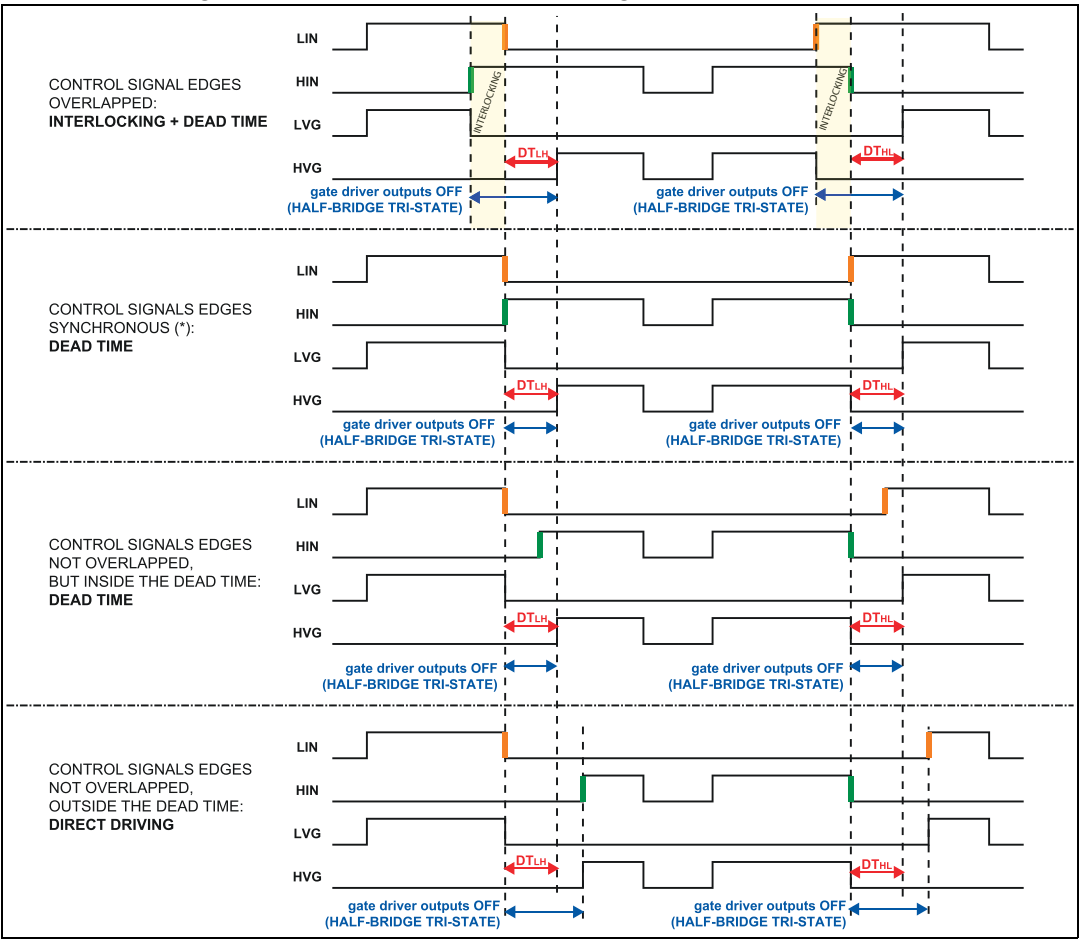


Figure 8. NTC resistance vs. temperature (zoom)



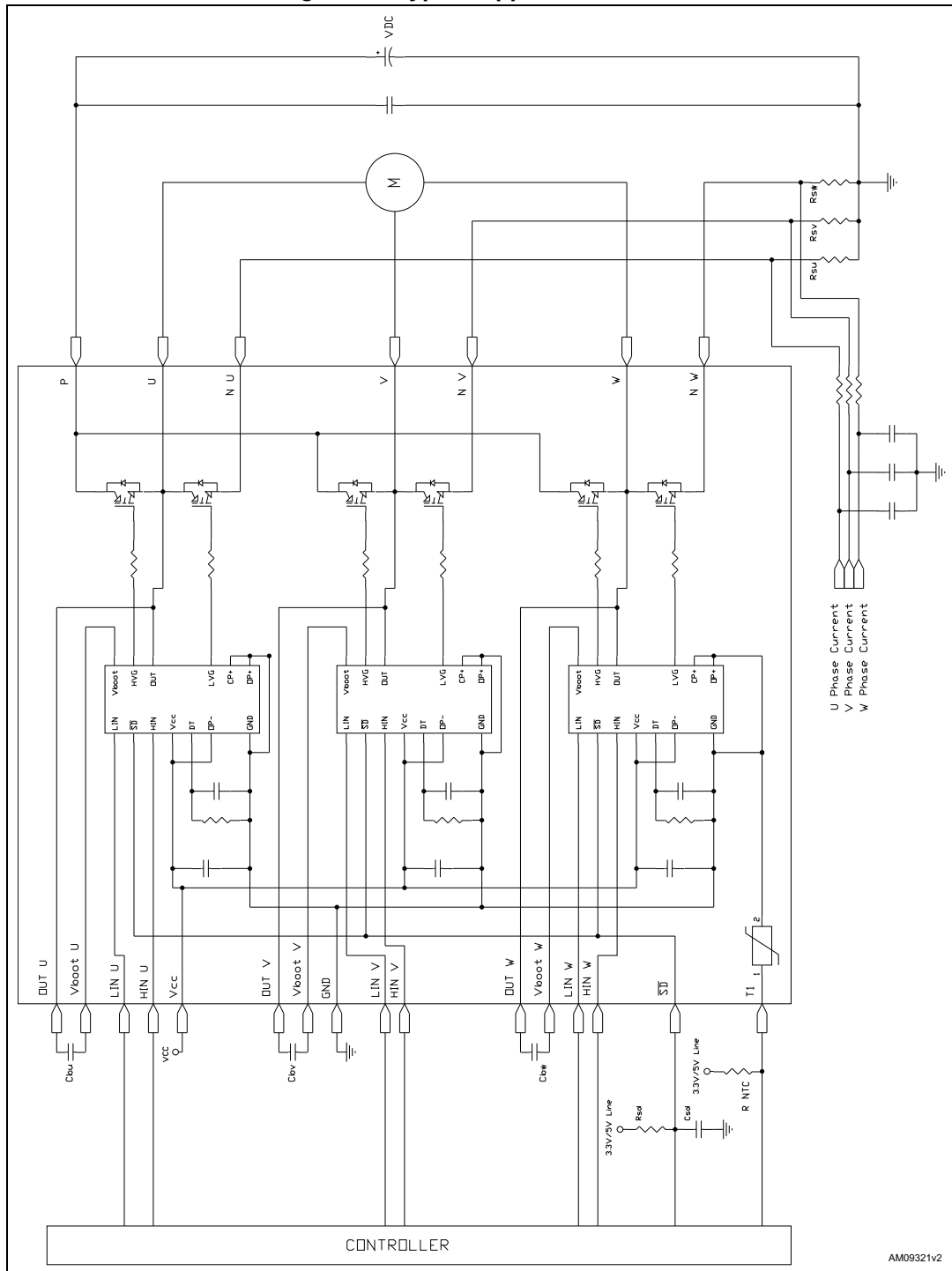
3.2 Waveform definitions

Figure 9. Dead time and interlocking waveform definitions



4 Applications information

Figure 10. Typical application circuit



4.1 Recommendations

- Input signals HIN, LIN are active high logic. A 375 k Ω (typ.) pull down resistor is built-in for each input. If an external RC filter is used, for noise immunity, pay attention to the variation of the input signal level.
- To prevent the input signals oscillation, the wiring of each input should be as short as possible.
- By integrating an application specific type HVIC inside the module, direct coupling to MCU terminals without any opto-coupler is possible.
- Each capacitor should be located as nearby the pins of IPM as possible.
- Low inductance shunt resistors should be used for phase leg current sensing.
- Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
- The $\overline{\text{SD}}$ signal should be pulled up to 5 V / 3.3 V with an external resistor.

Table 14. Recommended operating conditions

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max.	
V_{PN}	Supply voltage	Applied between P-Nu, Nv, Nw		300	400	V
V_{CC}	Control supply voltage	Applied between V_{CC} -GND	13.5	15	18	V
V_{BS}	High side bias voltage	Applied between V_{BOOTi} - OUT_i for $i = U, V, W$	13		18	V
t_{dead}	Blanking time to prevent arm-short	For each input signal	1			μs
f_{PWM}	Pwm input signal	-40°C < T_c < 100°C -40°C < T_j < 125°C			20	kHz
T_c	Case operation temperature				100	°C

For further details refer to AN3338.

5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Please refer to dedicated technical note TN0107 for mounting instructions.

5.1 SDIP-25L package information

Figure 11. SDIP-25L package outline

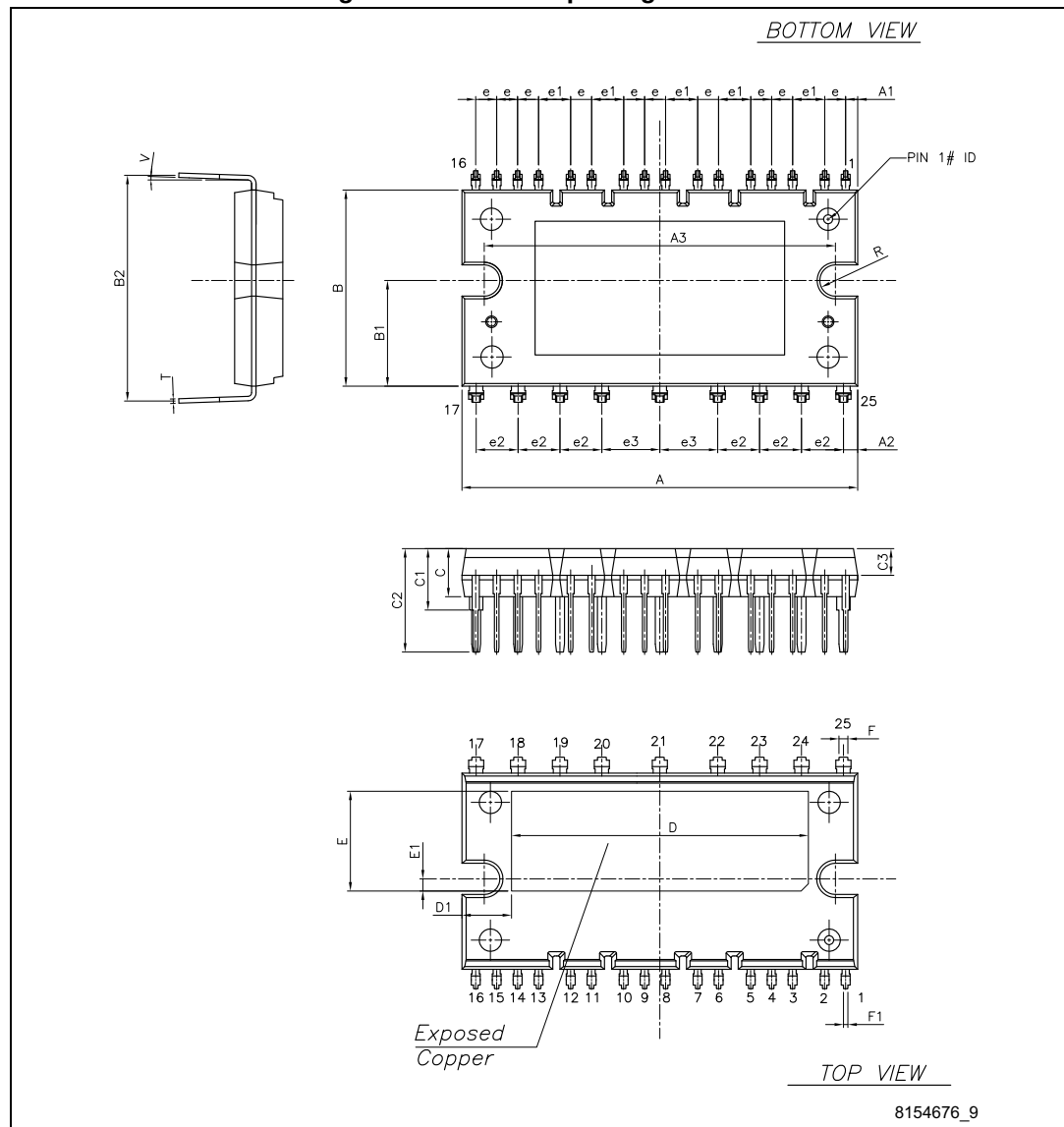
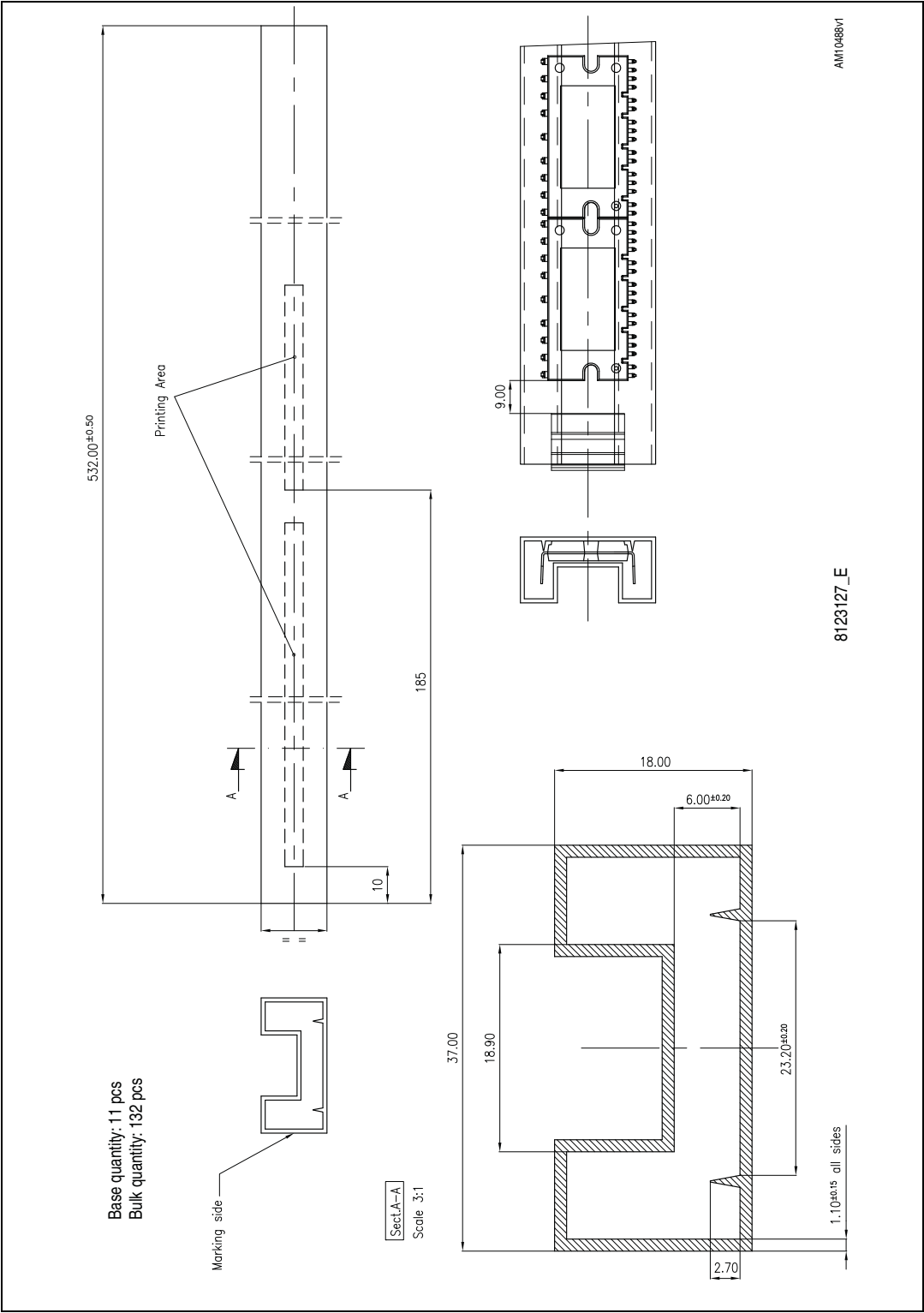


Table 15. SDIP-25L mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	43.90	44.40	44.90
A1	1.15	1.35	1.55
A2	1.40	1.60	1.80
A3	38.90	39.40	39.90
B	21.50	22.00	22.50
B1	11.25	11.85	12.45
B2	24.83	25.23	25.63
C	5.00	5.40	6.00
C1	6.50	7.00	7.50
C2	11.20	11.70	12.20
C3	2.90	3.00	3.10
e	2.15	2.35	2.55
e1	3.40	3.60	3.80
e2	4.50	4.70	4.90
e3	6.30	6.50	6.70
D		33.30	
D1		5.55	
E		11.20	
E1		1.40	
F	0.85	1.00	1.15
F1	0.35	0.50	0.65
R	1.55	1.75	1.95
T	0.45	0.55	0.65
V	0°		6°

5.2 Packing information

Figure 12. SDIP-25L packing information



6 Revision history

Table 16. Document revision history

Date	Revision	Changes
18-Jan-2013	1	Initial release.
15-Feb-2013	2	Added Inductive load typical value Table 7 on page 7 and Figure 8 on page 11 . Modified Figure 3 on page 8 and Figure 7 on page 11 .
05-Mar-2013	3	Modified Figure 7 and Figure 8 on page 11 .
15-Apr-2014	4	Document status changed from preliminary to production data. Updated Figure 2: Pin layout (bottom view) .
14-Apr-2015	5	Text edits and formatting changes throughout document Updated Figure 2: Pin layout (bottom view) Updated Section 5: Package information

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